

AMENDMENTS

In the Specification

Please amend paragraph 0048 as follows:

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0048 Notable within the planar spiral inductor structure of the present invention as illustrated within the schematic cross-sectional diagram of Fig. 3 is that the bond wire 15 has incorporated therein additional lead length, in particular as illustrated within the context of several loops (i.e., a minimum of one loop and preferably a plurality of loops), compressed in a location near the spirally patterned conductor layer 12d which forms the bond pad 14. Within the present invention, the presence of the lead length within the bond wire 15 with the minimum of one loop and preferably the plurality of loops at the location near the spirally patterned conductor layer 12d which forms the bond pad 14 provides for an additional tunable inductance when fabricating a microelectronic inductor structure in accord with the present invention. Typically and preferably, the lead length within the bond wire is formed of a length from about 1000 to about 100000 microns, to provide a tunable inductance to the microelectronic inductor structure whose schematic cross-sectional diagram is illustrated in Fig. 3 of from about 0.5 to about 5 nano-Henry in addition to a base inductance of the planar spiral inductor structure as illustrated within the schematic plan view diagram of Fig. 1 of from about 0.5 to about 30 nano-Henry.